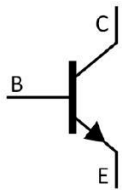


TO-92LM NPN Silicon NPN transistor in a TO-92LM Plastic Package.

KTA1023

Complementary pair with KTA1023.

High voltage application.

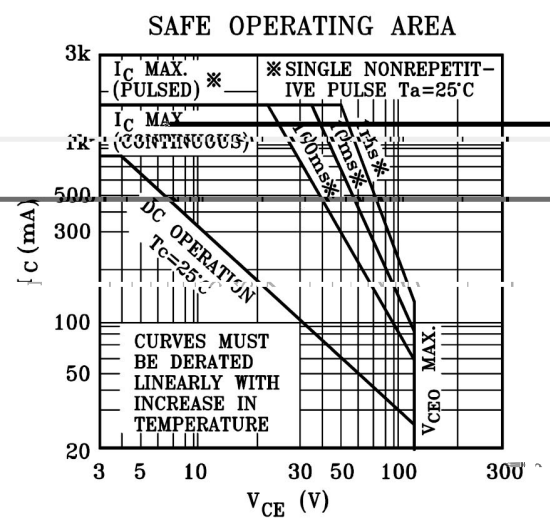
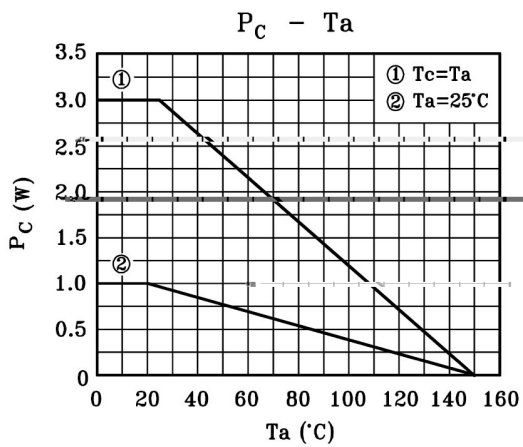
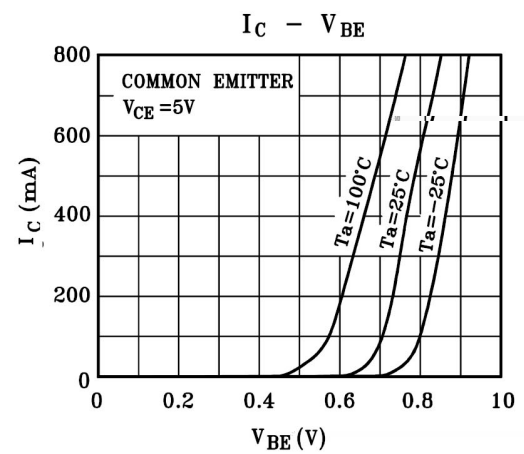
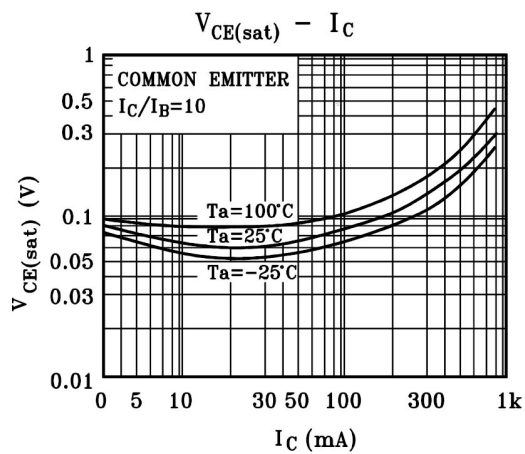
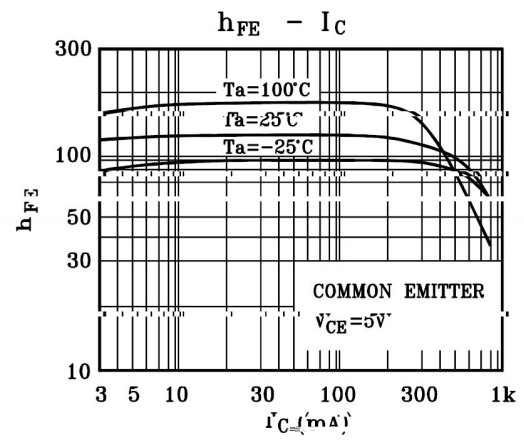
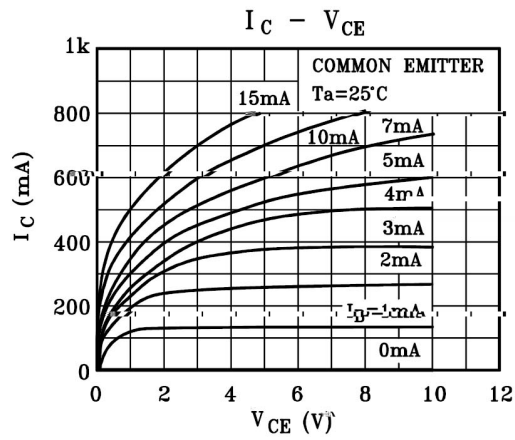


PIN1 Base PIN 2 Collector PIN 3 Emitter

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	80~160	120~240

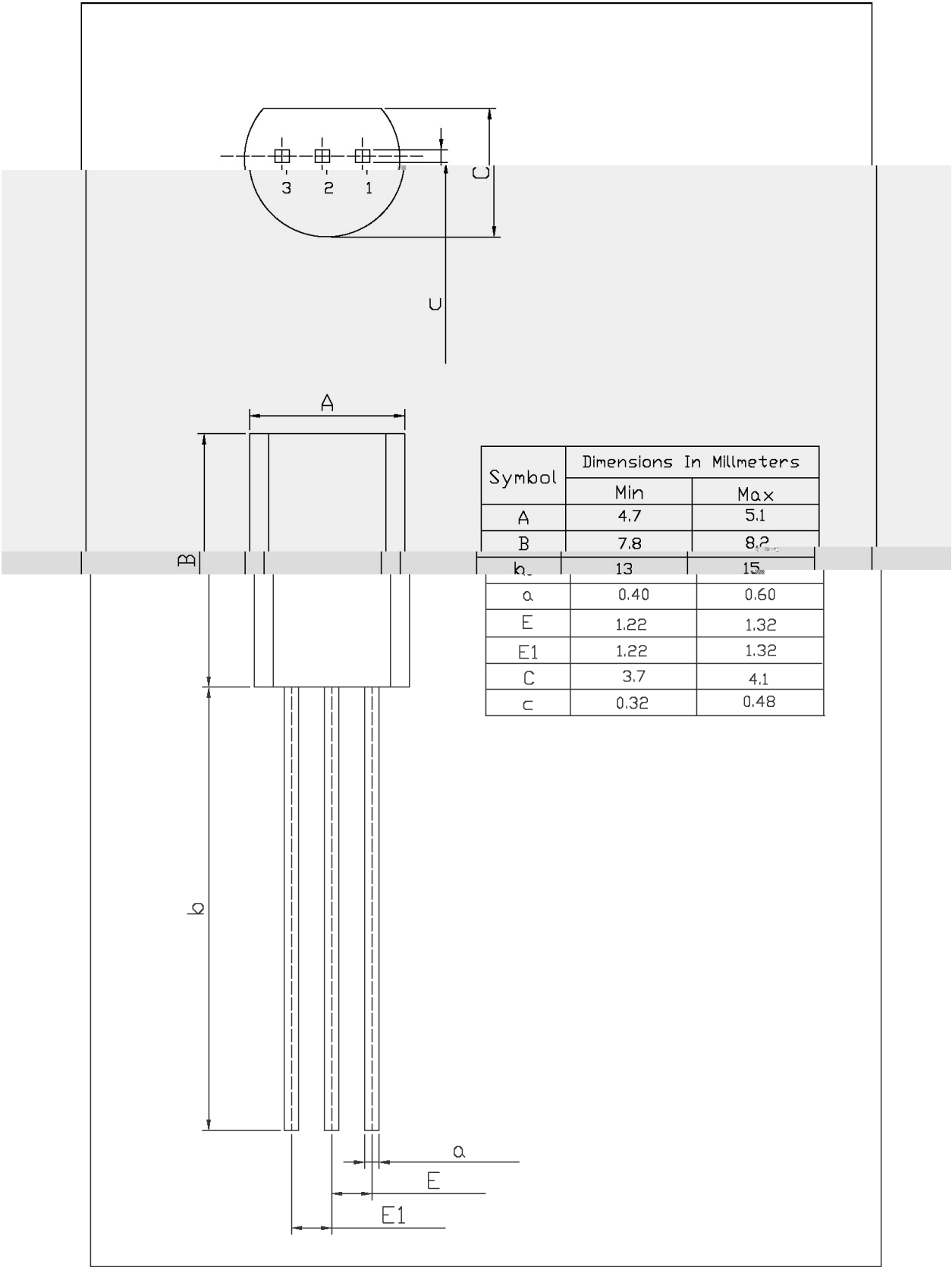
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	120	V
Collector to Emitter Voltage	V_{CEO}	120	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	800	mA
Emitter Current - Continuous	I_E	-800	mA
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55~150	

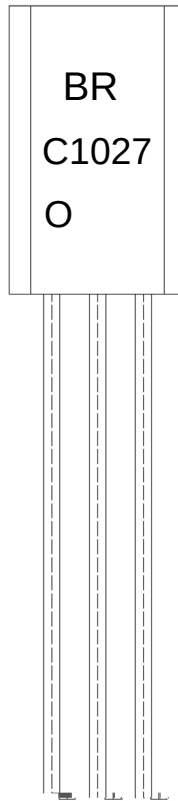
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	120			V
Collector to Base Breakdown Voltage	V_{EBO}	$I_E=1mA$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=120V$ $I_E=0$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5V$ $I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=5.0V$ $I_C=100mA$	80		240	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA$ $I_B=50mA$			1.0	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=5.0V$ $I_C=500mA$			1.0	V
Transition Frequency	f_T	$V_{CE}=5.0V$ $I_C=100mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$			30	pF



TO-92LM

Unit: mm





BR:

C1027

O: h_{FE}

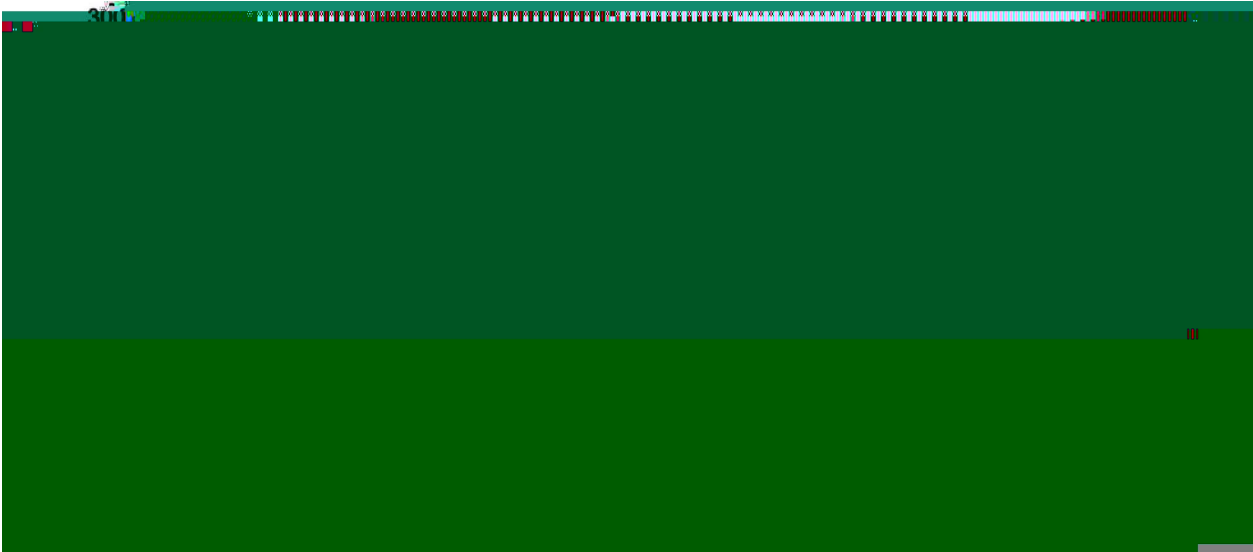
Note:

BR: Company Code.

C1027: Product Type.

O: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;

2

255±5

5±0.5sec;

3

2 10

/sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type	Units					Dimension		(unit mm3)

/ AMMO

Package Type	Units					Dimension		(unit mm3)